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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/360,292
Filing Date ..... July 22, 1999
Inventor ..... Sharan et al.
Assignee ..... Micron Technology, Inc.
Group Art Unit 1765
Examiner ..... Shamim Ahmed
Attorney's Docket No. MI22-1106
Title: Plasma Etching Process

RESPONSE TO JULY 8, 2002 FINAL OFFICE ACTION ACCOMPANYING CPA FILING

To: Box CPA
Assistant Commissioner for Patents
Washington, D.C. 20231

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AMENDMENTS

In the Specification

Please replace the abstract with the following clean replacement abstract in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

--In one implementation, a plasma etching process includes etching a carbon containing material from a substrate using a hydrogen or oxygen containing plasma. In one implementation, a plasma etching process includes forming openings in a masking layer over a substrate, etching through a material beneath the masking layer through the openings, and removing the masking layer. The substrate is then plasma etched at a temperature of at least 400°C. In one implementation, a semiconductor plasma etching process includes forming an undesired residue at least partially over the substrate during

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a first etching, and plasma etching the undesired residue from the substrate. In one implementation, a process of depositing a material over a semiconductor substrate includes plasma etching a substrate within the a reactor using a first gas chemistry and depositing a material over the substrate using a second gas chemistry without removing the substrate from the reactor. --

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In the Claims

None.